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June 2015

# FPAM50LH60 PFC SPM® 2 Series for 2-Phase Interleaved PFC

## **Features**

- UL Certified No.E209024 (UL1557)
- 600 V 50 A 2-Phase Interleaved PFC with Integral Gate Driver and Protection
- Very Low Thermal Resistance Using Al<sub>2</sub>O<sub>3</sub> DBC Substrate
- Full-Wave Bridge Rectifier and High-Performance Output Diode
- Optimized for 20kHz Switching Frequency
- Built-in NTC Thermistor for Temperature Monitoring
- Isolation Rating: 2500 V<sub>rms</sub>/min

### **Applications**

• 2-Phase Interleaved PFC Converter

## **General Description**

The FPAM50LH60 is a PFC SPM® 2 module providing a fully-featured, high-performance Interleaved PFC (Power Factor Correction) input power stage for consumer, medical, and industrial applications. These modules integrate optimized gate drive of the built-in IGBTs to minimize EMI and losses, while also providing multiple on-module protection features including under-voltage lockout, over-current shutdown, thermal monitoring, and fault reporting. These modules also feature a full-wave rectifier and high-performance output diodes for additional space savings and mounting convenience.

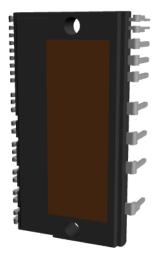


Fig. 1. 3D Package Drawing (Click to Activate 3D Content)

#### Package Marking and Ordering Information

| Device     | Device Marking | Package   | Packing Type | Quantity |
|------------|----------------|-----------|--------------|----------|
| FPAM50LH60 | FPAM50LH60     | S32EA-032 | Rail         | 8        |

## Integrated Drive, Protection and System Control Functions

- For IGBTs: gate drive circuit, Over-Current Protection (OCP), control supply circuit Under-Voltage Lock-Out (UVLO) Protection
- Fault signal: corresponding to OC and UV fault
- Built-in thermistor: temperature monitoring
- Input interface : active-HIGH interface, works with 3.3 / 5 V logic, Schmitt trigger input

## **Pin Configuration**

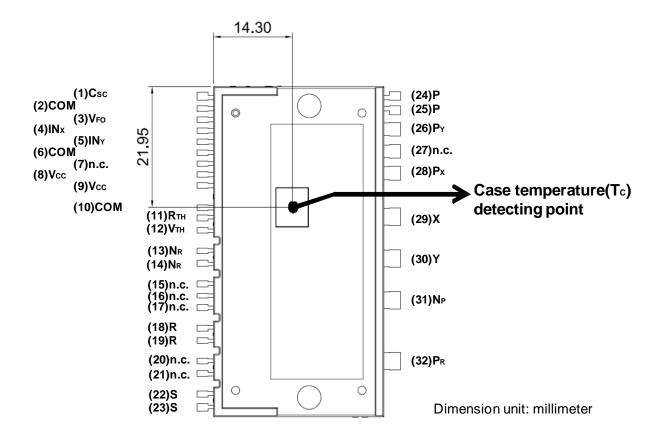


Figure 2. Top View

## **Pin Descriptions**

| Pin Number | Pin Name        | Pin Description                            |
|------------|-----------------|--|
| 1          | C <sub>SC</sub> | Signal Input for Over-Current Detection    |
| 2,6,10     | СОМ             | Common Supply Ground                       |
| 3          | V <sub>FO</sub> | Fault Output                               |
| 4          | IN <sub>X</sub> | PWM Input for X IGBT Drive                 |
| 5          | $IN_Y$          | PWM Input for Y IGBT Drive                 |
| 7          | N.C             | No Connection                              |
| 8,9        | V <sub>CC</sub> | Common Supply Voltage of IC for IGBT Drive |
| 11         | R <sub>TH</sub> | Series Resistor for The Use of Thermistor  |
| 12         | $V_{TH}$        | Thermistor Bias Voltage                    |
| 13,14      | N <sub>R</sub>  | Negative DC-Link of Rectifier Diode        |
| 15,16,17   | N.C             | No Connection                              |
| 18,19      | R               | AC Input for R-Phase                       |
| 20,21      | N.C             | No Connection                              |
| 22,23      | S               | AC Input for S-Phase                       |
| 24,25      | Р               | Output of Diode                            |
| 26         | P <sub>Y</sub>  | Input of Diode                             |
| 27         | N.C             | No Connection                              |
| 28         | P <sub>X</sub>  | Input of Diode                             |
| 29         | Х               | Output of X Phase IGBT                     |
| 30         | Υ               | Output of Y Phase IGBT                     |
| 31         | N <sub>P</sub>  | Negative DC-Link of IGBT                   |
| 32         | P <sub>R</sub>  | Positive DC-Link of Rectifier Diode        |

## **Internal Equivalent Circuit**

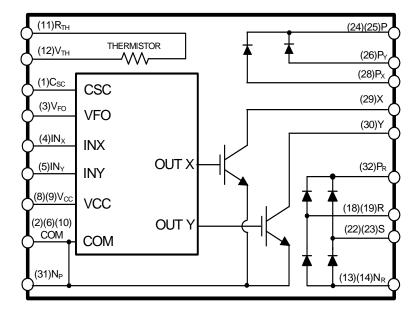


Figure 3. Internal Block Diagram

## **Absolute Maximum Ratings** ( $T_J = 25$ °C, unless otherwise specified.)

#### **Converter Part**

| Symbol                 | Parameter                                    | Conditions  | Rating    | Unit      |
|------------------------|--|---|-----------|-----------|
| V <sub>i</sub>         | Input Supply Voltage                         | Applied between R - S   | 264       | $V_{rms}$ |
| V <sub>PN</sub>        | Output Voltage                               | Applied between X - N <sub>P</sub> , Y - N <sub>P</sub> , P - P <sub>X</sub> , P - P <sub>Y</sub>         | 450       | V         |
| V <sub>PN(Surge)</sub> | Output Supply Voltage (Surge)                | Applied between X - N <sub>P</sub> , Y - N <sub>P</sub> , P - P <sub>X</sub> , P - P <sub>Y</sub>         | 500       | V         |
| V <sub>CES</sub>       | Collector-emitter Voltage                    | Breakdown Voltage between X - N <sub>P</sub> , Y - N <sub>P</sub>   | 600       | V         |
| V <sub>RRM</sub>       | Repetitive Peak Reverse Voltage of FRD       | Breakdown Voltage between P - P <sub>X</sub> , P - P <sub>Y</sub>   | 600       | V         |
| V <sub>RRMR</sub>      | Repetitive Peak Reverse Voltage of Rectifier | Breakdown Voltage between P <sub>R</sub> - R, P <sub>R</sub> - S, R - N <sub>R</sub> , S - N <sub>R</sub> | 900       | V         |
| *I <sub>F</sub>        | FRD Forward Current                          | T <sub>C</sub> = 25°C, T <sub>J</sub> < 125°C   | 50        | Α         |
| *I <sub>FSM</sub>      | Peak Surge Current of FRD                    | Non-Repetitive, 60 Hz Single Half-Sine Wave   | 500       | Α         |
| *I <sub>FR</sub>       | Rectified Forward Current                    | T <sub>C</sub> = 25°C, T <sub>J</sub> < 125°C   | 50        | Α         |
| *I <sub>FSMR</sub>     | Peak Surge Current of Rectifier              | Non-Repetitive, 60 Hz Single Half-Sine Wave   | 500       | Α         |
| ± *I <sub>C</sub>      | Each IGBT Collector Current                  | T <sub>C</sub> = 25°C, T <sub>J</sub> < 125°C   | 50        | Α         |
| ±*I <sub>CP</sub>      | Each IGBT Collector Current(Peak)            | T <sub>C</sub> = 25°C, T <sub>J</sub> < 125°C,<br>Under 1 ms Pulse Width                                  | 100       | Α         |
| *P <sub>C</sub>        | Collector Dissipation                        | T <sub>C</sub> = 25°C per IGBT  | 135       | W         |
| T <sub>J</sub>         | Operating Junction Temperature               | (1st Note 1)  | -40 ~ 125 | °C        |

#### 1st Notes

#### **Control Part**

| Symbol          | Parameter                     | Conditions  | Rating                       | Unit |
|-----------------|-------------------------------|---|------------------------------|------|
| V <sub>CC</sub> | Control Supply Voltage        | Applied between V <sub>CC</sub> - COM                   | 20                           | V    |
| V <sub>IN</sub> | Input Signal Voltage          | Applied between IN <sub>X</sub> , IN <sub>Y</sub> - COM | -0.3 ~ V <sub>CC</sub> + 0.3 | V    |
| $V_{FO}$        | Fault Output Supply Voltage   | Applied between V <sub>FO</sub> - COM                   | -0.3 ~ V <sub>CC</sub> + 0.3 | V    |
| I <sub>FO</sub> | Fault Output Current          | Sink Current at V <sub>FO</sub> Pin                     | 1                            | mA   |
| V <sub>SC</sub> | Current Sensing Input Voltage | Applied between C <sub>SC</sub> - COM                   | -0.3 ~ V <sub>CC</sub> + 0.3 | V    |

## **Total System**

| Symbol           | Parameter           | Conditions  | Rating    | Unit             |
|------------------|---------------------|---|-----------|------------------|
| T <sub>STG</sub> | Storage Temperature |   | -40 ~ 125 | ç                |
| V <sub>ISO</sub> | Isolation Voltage   | 60 Hz, Sinusoidal, AC 1 Minute, Connect Pins to Heat-Sink Plate | 2500      | V <sub>rms</sub> |

## **Thermal Resistance**

| Symbol                | Parameter                | Condition                                | Min. | Тур. | Max. | Unit |
|-----------------------|--------------------------|--|------|------|------|------|
| R <sub>th(j-c)Q</sub> | Junction to Case Thermal | Each IGBT under Operating Condition      | ı    | -    | 0.74 | °C/W |
| R <sub>th(j-c)D</sub> | Resistance               | Each Diode under Operating Condition     | 1    | -    | 1.13 | °C/W |
| R <sub>th(j-c)R</sub> |                          | Each Rectifier under Operating Condition | 1    | -    | 0.74 | °C/W |

<sup>1.</sup> The maximum junction temperature rating of the power chips integrated within the PFC SPM  $^{\! @}$  product is 125  $^{\circ}$  C.

<sup>2.</sup> Marking " \* " is calculation value or design factor.

## **Electrical Characteristics** ( $T_J = 25$ °C, unless otherwise specified.)

#### **Converter Part**

| Symbol               | Parameter                              | Conditions   | Min. | Тур. | Max. | Unit |
|----------------------|--|--|------|------|------|------|
| V <sub>CE(SAT)</sub> | IGBT Saturation Voltage                | V <sub>CC</sub> = 15 V, V <sub>IN</sub> = 5 V, I <sub>C</sub> = 50 A                       | -    | 1.7  | 2.2  | V    |
| V <sub>FF</sub>      | FRD Forward Voltage                    | I <sub>F</sub> = 50 A  | -    | 1.9  | 2.4  | V    |
| $V_{FR}$             | Rectifier Forward Voltage              | I <sub>FR</sub> = 50 A   | -    | 1.13 | 1.35 | V    |
| I <sub>RR</sub>      | Switching Characteristic               | $V_{PN} = 400 \text{ V}, V_{CC} = 15 \text{ V}, I_{C} = 25 \text{ A},$                     | -    | 27   | -    | Α    |
| t <sub>RR</sub>      |  | $V_{IN} = 0 \text{ V} \leftrightarrow 5 \text{ V}$ , Inductive Load (1st Note 3), per IGBT | -    | 55   | -    | ns   |
| t <sub>ON</sub>      |  |  | -    | 772  | -    | ns   |
| t <sub>OFF</sub>     |  |  | -    | 1117 | -    | ns   |
| t <sub>C(ON)</sub>   |  |  | -    | 110  | -    | ns   |
| t <sub>C(OFF)</sub>  |  |  | -    | 125  | -    | ns   |
| I <sub>CES</sub>     | Collector - Emitter<br>Leakage Current | V <sub>CES</sub> = 600 V   | -    | -    | 250  | μА   |

#### 1st Notes:

<sup>3.</sup> t<sub>ON</sub> and t<sub>OFF</sub> include the propagation delay of the internal drive IC. t<sub>C(ON)</sub> and t<sub>C(OFF)</sub> are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.

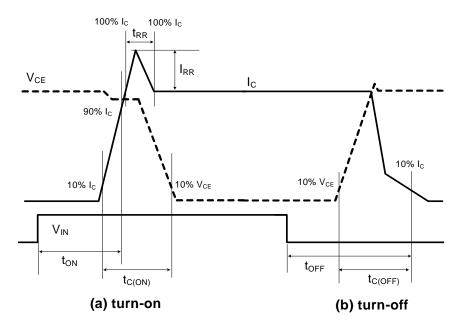


Figure 4. Switching Time Definition

#### **Control Part**

| Symbol               | Parameter  | Conditions   | Min. | Тур. | Max. | Unit |
|----------------------|--|--|------|------|------|------|
| I <sub>QCC</sub>     | Quiescent V <sub>CC</sub> Supply<br>Current              | $V_{CC}$ = 15 V, $IN_X$ , $IN_Y$ - $COM$ = 0 V, Supply current between $V_{CC}$ and $COM$  | -    | -    | 2.65 | mA   |
| I <sub>PCC</sub>     | Operating V <sub>CC</sub> Supply<br>Current              | $V_{CC}$ = 15 V, $f_{PWM}$ = 20 kHz, Duty = 50%<br>Applied to One PWM Signal Input per IGBT<br>Supply Current between $V_{CC}$ and COM | -    | -    | 7.0  | mA   |
| $V_{FOH}$            | Fault Output Voltage                                     | $V_{SC} = 0 \text{ V}, V_{FO} \text{ Circuit: } 10 \text{ k}\Omega \text{ to 5 V Pull-up}$   | 4.5  | -    | -    | V    |
| V <sub>FOL</sub>     |  | $V_{SC}$ = 1 V, $V_{FO}$ Circuit: 10 k $\Omega$ to 5 V Pull-up   | -    | -    | 0.5  | V    |
| V <sub>SC(Ref)</sub> | Over-Current Protection Trip<br>Level Voltage of CSC Pin | V <sub>CC</sub> = 15 V   | 0.45 | 0.5  | 0.55 | V    |
| UV <sub>CCD</sub>    | Supply Circuit Under-                                    | Detection Level  | 10.5 | -    | 13.0 | V    |
| UV <sub>CCR</sub>    | Voltage Protection                                       | Reset Level  | 11.0 | -    | 13.5 | V    |
| t <sub>FOD</sub>     | Fault-Out Pulse Width                                    |  | 30   | -    | -    | μS   |
| V <sub>IN(ON)</sub>  | ON Threshold Voltage                                     | Applied between IN <sub>X</sub> , IN <sub>Y</sub> - COM  | 2.6  | -    | -    | V    |
| V <sub>IN(OFF)</sub> | OFF Threshold Voltage                                    | Applied between IN <sub>X</sub> , IN <sub>Y</sub> - COM  | -    | -    | 0.8  | V    |
| R <sub>TH</sub>      | Resistance of Thermistor                                 | at T <sub>TH</sub> = 25°C (1st Note 4, Figure 5)   | -    | 47   | -    | kΩ   |
|                      |  | at T <sub>TH</sub> = 100°C (1st Note 4, Figure 5)  | -    | 2.9  | -    | kΩ   |

#### 1st Notes

 $<sup>4.\</sup> T_{TH}\ is\ the\ temperature\ of\ thermister\ itself.\ To\ know\ case\ temperature\ (\ T_C),\ please\ make\ the\ experiment\ considering\ your\ application.$ 

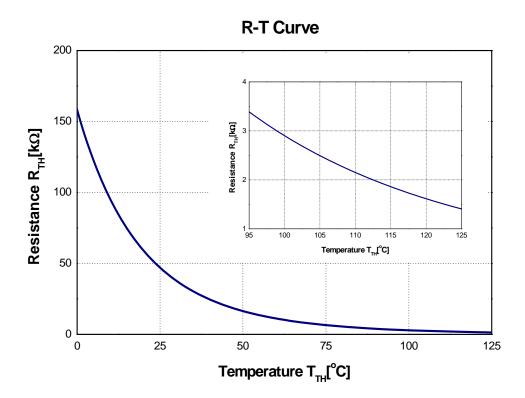


Figure 5. R-T Curve of The Built-in Thermistor

## $\label{eq:commended Operating Conditions} \ \ (T_J = 25^{\circ}C, \ unless \ otherwise \ specified.)$

| Symbol               | Parameter Conditions   |   | Min. | Тур. | Max. | Unit             |
|----------------------|------------------------|---|------|------|------|------------------|
| V <sub>i</sub>       | Input Supply Voltage   | Applied between R - S   | 187  | -    | 253  | V <sub>rms</sub> |
| l <sub>i</sub>       | Input Current          | $T_C < 100$ °C, $V_i = 220$ V, $V_O = 360$ V, $f_{PWM} = 20$ kHz per IGBT                         | -    | -    | 35   | A <sub>rms</sub> |
| V <sub>PN</sub>      | Supply Voltage         | Applied between X - N <sub>P</sub> , Y - N <sub>P</sub> , P - P <sub>X</sub> , P - P <sub>Y</sub> | -    | -    | 400  | V                |
| V <sub>CC</sub>      | Control Supply Voltage | Applied between V <sub>CC</sub> - COM   | 13.5 | 15.0 | 16.5 | V                |
| dV <sub>CC</sub> /dt | Supply Variation       |   |      | -    | 1    | V/μs             |
| I <sub>FO</sub>      | Fault Output Current   | Sink Current at V <sub>FO</sub> Pin   | -    | -    | 1    | mA               |
| f <sub>PWM</sub>     | PWM Input Frequency    | -40°C < T <sub>J</sub> < 125°C per IGBT   | -    | 20   | -    | kHz              |

## **Mechanical Characteristics and Ratings**

| Parameter       | Co                 | nditions             | Min. | Тур. | Max. | Unit       |
|-----------------|--------------------|----------------------|------|------|------|------------|
| Mounting Torque | Mounting Screw: M4 | Recommended 0.98 N•m | 0.78 | 0.98 | 1.17 | N•m        |
|                 |                    | Recommended 10 kg•cm | 8    | 10   | 12   | kg•cm      |
| Device Flatness | See Figure 6       |                      | 0    | -    | +150 | μ <b>m</b> |
| Weight          |                    |                      | -    | 32   | -    | g          |

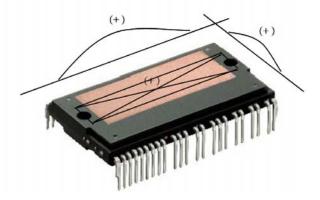
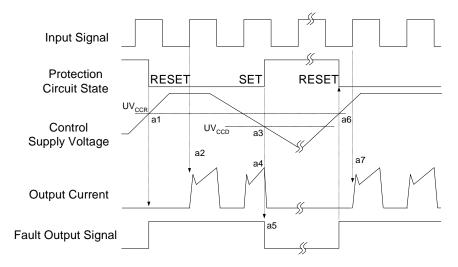


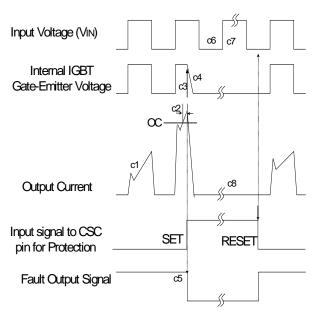
Figure 6. Flatness Measurement Position

#### **Time Charts of Protective Function**



- a1 : Control supply voltage rises: after the voltage rises UV<sub>CCR</sub>, the circuits start to operate when the next input is applied.
- a2: Normal operation: IGBT ON and carrying current.
- a3 : Under-voltage detection (UV<sub>CCD</sub>).
- a4: IGBT OFF in spite of control input condition.
- a5: Fault output operation starts.
- a6 : Under-voltage reset (UV $_{CCR}$ ).
- a7: Normal operation: IGBT ON and carrying current.

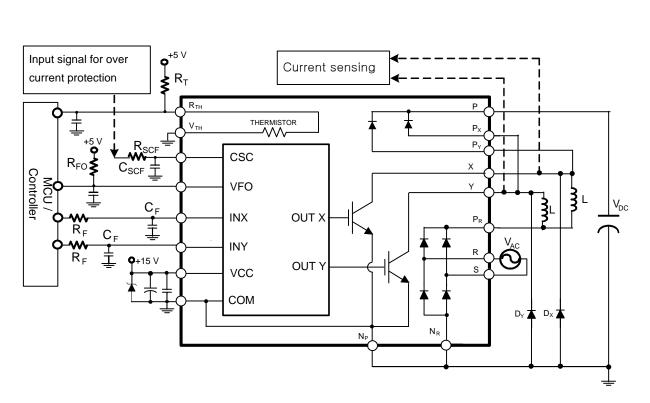
Figure 7. Under-Voltage Protection



(with the external over current detection circuit)

- c1: Normal operation: IGBT ON and carrying current.
- c2: Over-current detection (OC trigger).
- c3 : Hard IGBT gate interrupt.
- c4 : IGBT turns OFF.
- c5 : Fault output timer operation starts.
- c6 : Input "LOW": IGBT OFF state.
- c7 : Input "HIGH": IGBT ON state, but during the active period of fault output the IGBT doesn't turn ON.
- c8: IGBT OFF state.

**Figure 8. Over-Current Protection** 

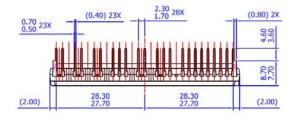


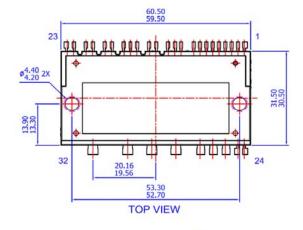
**Figure 9. Typical Application Circuit** 

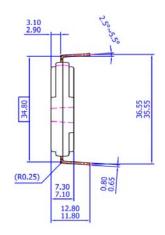
#### 2nd Notes:

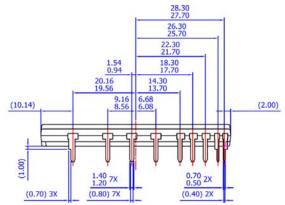
- 1. To avoid malfunction, the wiring of each input should be as short as possible(less than 2  $\sim$  3 cm).
- 2. V<sub>FO</sub> output is open-drain type. This signal line should be pulled up to the positive-side of the MCU or control power supply with a resistor that makes I<sub>FO</sub> up to 1 mA.
- 3. Input signal is active-HIGH type. There is a 5 k $\Omega$  resistor inside the IC to pull-down each input signal line to GND. RC coupling circuits is recommanded for the prevention of input signal oscillation. R<sub>F</sub>C<sub>F</sub> constant should be selected in the range 50~150ns (recommended R<sub>F</sub> = 100  $\Omega$ , C<sub>F</sub> = 1 nF).
- 4. To prevent error of the protection function, the wiring related with  $R_{SCF}$  and  $C_{SCF}$  should be as short as possible.
- 5. In the over current protection circuit, please select the  $R_{SCF}$ ,  $C_{SCF}$  time constant in the range 1.5 ~ 2  $\mu s$ .
- 6. Each capacitors should be mounted as close to the PFC  $\mathsf{SPM}^{\circledR}$  product pins as possible.
- 7. Relays are used at almost every systems of electrical equipments of home appliances. In these cases, there should be sufficient distance between the MCU / controller and the relays.
- 8. Internal NTC thermistor can be used for monitoring of the case temperature and protecting the device from the overheating operation. Select an appropriate resistor R<sub>T</sub> according to the application.
- 9. It is recommended that anti-parallel diode ( $D_X$  , $D_Y$ ) be connected with each IGBT.

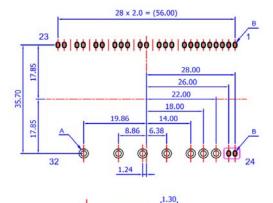
### **Detailed Package Outline Drawings**











NOTES: UNLESS OTHERWISE SPECIFIED
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- E) [ ] IS ASS'Y QUALITY
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LAND PATTERN RECOMMENDATIONS

DETAIL B

DETAIL A

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#### As used herein

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